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Date: January 7, 2004

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Fax Contains: _7_ pages (include	ling this sheet). If in	complete, call (650) 4	93-9300 x7255.
Message:			
In re Application of			
Stephen E. Savas Application No.: 10/053,138 Filed: 01/18/2002	Group Art Unit: 1 Examiner: Parvi:		
For: Pulsed Plasma Processing o	f Semiconductor Su	bstrates	
Please see attached Transmittal, I	Fee Transmittal, and	Response to Office	Action In the above-

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Ref: 14912.786

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			Application Number 10/053,138					
	Ti		MITTAL		Filing Date	January 18, 2002		
		FQ	RM		First Named Inventor	Stephen E. Savas		
(to	be used for	āli corresp	oondence after initial	filing)	Art	1763		
					Examiner	Parviz Hassa	nzader	<u> </u>
Tại	al Number ci	Pages in	This Submission	7	Attorney Docket Number	14912.786		
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	Response Incomplet	t(s) to Missi e Applice	•					•
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Firm r		Micha	el J. Murphy, F	Reg. No.	37,404; Customer No. 219	71		
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	Signature // // // // // // // // // // // // //							
Date January 7, 2004								
			C	ERTIFIC	ATE OF TRANSMISSION	/MAILING		
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Турес	Typed or printed Michael J. Murphy (via facsimile 703-872-9306)							
Signa	ture		Mi	10	n	•	Date	January 7, 2004

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FEE TRANSMITTAL				<u> </u>	Complete if Known						
for FY 2004						Application Number 10/053,138					
Patent fees are subject to annual revision.									Jan. 18, 2002		
Small Entity payments must be supported by a small entity statement,									Stephen E. Savas		
otherwise large entity fees must be pald. See Forms PTO/SB/09-12.  See 37 C.F.R. §§ 1.27 and 1.28.				Examiner Name  Group/Art Unit			Parviz Hassanzadeh				
TOTAL AMOU	NT OF PA	YMENT	(S) 950		<del></del>	1705					
					1	Attorney Docket Number 14912.786					
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Deposit					105	130	205	65	Surcharge - late filling fee or oath		
Account W Name	ilson Sonsi	mi Goodri	ich & Rosati		127	50	227	25	Surcharge - late provisional filing fee or cover sheet		
_					139	130	139	130	Non-English specification		
×		y Additiona CFR §§ 1.16	I Fee Required and 1.17		147	2,520		2,520	For filing a request for reexamination		
					112	920	112	920*	Requesting publication of SIR prior to Examiner action		
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		CALCUL	ATION		116	420	216	210	Extension for reply within second month		
1. BASIC FILI Large Entity		Entity	Fee Description	Fee Paid	117	950	217	475	Extension for reply within third month	950	
Fee Fee	Fee	Fee	ree Description	1691 970	118	1,480	218	740	Extension for reply within fourth month		
Code (S)	Code	<b>(S)</b>			128	2,010	228	1,005	Extension for reply within fifth month		
101 ,770	201	385	Utility filing fee		119	330	219	165	Natice of Appeal		
106 340	206	170	Design filing fee		120	330	220	165	Filing a brief in support of an appeal		
107 530	207	265	Plant filing fee		121	290	221	145	Request for oral hearing		
108 770	208	385	Reissue filing fcc		138	1,510	138	1,510	Petition to institute a public use proceeding		
114 160	214	80	Provisional filing [		140	110	240	55	Petition to revive - unavoidable		
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2. EXTRA CLA	IM FEES	Extra Cl	Fee from below	Fee Paid	142	1,330	242	665	Utility issue fee (or reissue)		
Total Claims	-20** =		_ x		143	480	243	240	Dosign issue fee		
Independent Claims	-3**=		_ x [		144	640	244	320	Plant iasue fee		
Multiple Dependen	t		=		122	130	122	130	Petitions to the Commissioner		
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Code (\$) 103 18	203	9	Claims in excess of 20	)	581	40	581	40	Recording each patent assignment per		
102 86	202	43	Independent claims in	excess of 3	146	770	246	385	property (times number of properties) Filing a submission after fina)		
104 290	204	145	Multiple dependent cla	aim, if not	149	770	249	385	rejection (37 CFR 1.129(a)) For each additional invention to be examined (37 CFR 1.129(b))		
109 86	209	43	**Reissue independen	nt claims	Other f	ee (specify	Α		CALIMINO (27 CFR 1.123(B))		
110 18	210	9	over original patent **Reissue claims in ex			èe (specif	•	55/110	Terminal Disclaimer		
20 and over original patent SUBTOTAL (2) (\$)0					sic Filing I		SUBTOTAL (3)	\$950			
SUBMITTED B	v								Complete		
Name (Print/Type)	Michael J	. Murphy			Registrati		37,404		Telephone 650-493-	9300	
Signature	4	3/	Olm	. 1	Date	January 7	, 2004		Customer No. 02197		
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Attorney Docket No. 14912,786

	IN THE UNITED STATES PATER	CENTRAL FAX CENTER		
In re A	Application of	) )	JAN 0 7 2004	
:	Stephen E. Savas	) Group Art Unit: 1763	OCCOM	
Appli	cation No.: 10/053,138	) Examiner: Parviz Hassanzadeh		
Filed:	01/18/2002	, ) )		
For:	Pulsed Plasma Processing of Semiconductor Substrates	, ) )		

## Response to Office Action

Mail Stop: Amendment Commissioner for Patents PO Box 1450 Alexandria VA 22313-1450

Sir:

In an office action dated July 7, 2003, the Examiner rejected pending claims 44-82. The Examiner rejected claims 44-56 and 60-63 under 103(a) as being unpatentable over U.S. Patent 5,289,010 ("Shohet") in view of WO 91/10341 ("Savas") and rejected claims 57-59 and 64-82 under 103(a) as being unpatentable over Shohet in view of Savas and further in view of U.S. Patent 4,858, 516 ("Corn"). In this response, applicant respectfully traverses the Examiner's rejection of pending claims 44-82.

Claims 44 and 64 are independent claims and claims 45-63 and claims 65-82 depend from those claims, respectively.

Claim 44 is directed at a method of plasma processing a semiconductor substrate comprising, among other things, inductively coupling power to a plasma using high power cycles and low power cycles such that greater than about 5kW of power is coupled to the plasma during each high power cycle; coupling power to a substrate support using high power cycles and low power cycles; and

synchronizing such that the high power cycles are applied to the substrate support substantially during the time that low power cycles are applied to the plasma.

Claim 64 is directed at a method of plasma processing a semiconductor substrate comprising, among other things, inductively coupling power to a plasma using high power cycles and low power cycles with a duty cycle of about 5 to 30 percent; coupling power to a substrate support using high power cycles and low power cycles; and synchronizing such that the high power cycles are applied to the substrate support substantially during the time that low power cycles are applied to the plasma.

In rejecting independent claims 44 and 64, the Examiner relies upon Shohet as teaching a plasma power source 36 modulated by a pulse modulator 38 such that "whereas as shown in Fig. 3, plasma excitation is on except during the time a pulsed voltage is applied to the substrate support".

Shohet describes a plasma source ion implantation process and apparatus. A plasma may be created by ionizing a neutral gas. However, unwanted species may also be ionized when generating the plasma. See col. 1, lines 65-67 and col. 2, lines 9-10 and 17-21. Shohet teaches the use of ion cyclotron resonance (ICR) in the presence of a magnetic field to purify the ions and drive unwanted ion species into resonance and into a collection plate or other collection means. See col. 2, lines 21-30. The frequency, magnetic field, electric field and other parameters are selected in relation to one another to achieve the desired resonance and resulting purification. See col. 4, lines 6-68 and col. 5, lines 1-24. In Figures 1 and 2 of Shohet, a magnet 22 provides a magnetic field between plate-like electrodes 17 and plates 19 to form the ICR system. This ICR system is separate from the plasma source 16 and plasma source power supply 36 used to ionize the gas.

Figure 3 in Shohet, referenced by the Examiner, illustrates acceleration pulses 61 applied to the target and the ICR excitation 64 and 69 which are applied to the excitation electrodes 17. See col. 7, lines 39-51. The ICR excitation signals 64 and 69 in Figure 3 are the signals used to purify ions after the plasma is generated and are not signals used to generate the plasma. See also col. 6, lines 14-20

(the plasma source 16 creates the plasma which drifts into the ion purification region and "Once the ions are in the ion purification region, the time varying electric field from the excitation electrode 17 serves to sweep out the undesired species").

While the ICR in Shohet applies an excitation signal to the plasma, it uses a magnet and platelike electrodes (and the corresponding excitation signals in Figure 3 of Shohet) and does not teach or
suggest inductively coupling power into the plasma in the manner set forth in independent claims 44
and 64 of the present application. Moreover, there is no suggestion to substitute the plasma source or
power signals in Savas for the ICR purification in Shohet. Shohet teaches that the frequency, magnetic
field, electric field and other parameters are selected in relation to one another to achieve the desired
resonance. There is no teaching or suggestion to combine the higher power levels of Savas cited by the
Examiner to the ion purification excitation signals in Figure 3 of Shohet. In addition, the plasma
source in Savas does not purify ions for ion implantation as desired in Shohet and substituting it for the
ICR in Shohet would render Shohet inoperable for its intended purpose. In addition, substituting the
plasma source in Savas for the plasma source in Shohet also would not result in the claimed invention,
because the excitation signals shown in Figure 3 do not apply to the power source (and, in any event,
the plasma source of Savas does not use high and low power cycles of the type required by
independent claims 44 and 64).

Corn also does not make up for the deficiencies in Shohet. Corn describes parallel plate electrodes which would capacitively (rather than inductively) couple power into a plasma. High and low frequency signals are applied to the electrodes for an etch process. Corn does not teach or suggest inductively coupling power into a reactor in the manner set forth in independent claims 44 and 64. In addition, there is no suggestion to combine the duty cycles used for the etch process in Corn with the ion implantation reactor described in Shohet. The ion implantation reactor uses high voltage

acceleration pulses to implant ions and does not use dual RF frequency signals of the type used for etching in Corn.

Methods using inductively coupled plasmas in accordance with the claimed invention can be used to provide important advantages by reducing charge build up and microsteering, a problem not recognized or addressed by the above references.

In view of the above, applicant believes that independent claims 44 and 64 are not anticipated or rendered obvious by Shohet either alone or in view of Savas and Corn. Therefore, claims 44 and 64 are believed to be patentable. Claims 45-63 and claims 65-82 depend from independent claims 44 and 64 and, as a result, are also believed to be patentable.

In view of the foregoing, it is believed that all of the pending claims are in condition for allowance. Applicant respectfully requests reconsideration, allowance and passage to issue of the claims as amended.

The Commissioner is authorized to charge any additional fees which may be required, including petition fees, or credit any overpayment to Deposit Account No. 23-2415 (Docket No. 14912-786).

Respectfully submitted,

WILSON SONSINI GOODRICH & ROSATI

Date: January 7, 2004

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